

Application Note

AN-TDA16888-0-010323

TDA 16888: Multioutput Single Transistor Forward Converter 150W / 100kHz

Author: Michael Herfurth

Published by Infineon Technologies AG

<http://www.infineon.com>

Power Management & Supply



N e v e r s t o p t h i n k i n g

150W Output: 5V/18A; 12V/4A; -12V/1A; Standby: 5V/100mA

Operating Frequency: 100kHz

Contents:

1. Circuit description.....	3
2. Circuit diagram.....	6
3. Test results.....	7
4. Bill of materials.....	8
5. Control PCB layout.....	11
6. Power PCB layout.....	12
7. Transformer design.....	13
8. Smoothing choke design.....	14
9. Boost inductor design.....	15
10. RFI choke design.....	16
11. Picture of testboard.....	17

Circuit description

Multioutput single transistor forward converter with boost PFC preconverter

The power supply for a PC using up to 150 W of power must, for example, provide the following voltages: 5V/18A; 12V/4A; -12V/0.7A; -5V/0.3A; and Standby 5V/0.1A. If any of the mains systems in use around the world may be used as a power source, then an input voltage range of 90V to 270V AC is required, taking into account the relevant tolerances.

The application circuit using the TDA 16888 is able to cover universal input voltage range mentioned above (if required). In this circuit a boost converter (Q1, L2, D5, C3) works as an active harmonic filter to provide power factor correction, intermediate circuit voltage stabilization and to supply the primary and secondary side control logic in normal and standby operation. In addition, the bridging time for dips in the mains voltage is not dependent on the mains voltage level. How the IC works in a typical application circuit is described below.

Start up

When the mains voltage is switched on, the smoothing capacitor C3 is charged by a current pulse, the current being limited by the winding resistances of the chokes and NTC resistor R36. Start-up capacitor C11A is charged by a low current (<1mA) through resistors R2 and R43. Once the switch-on threshold (14V) is reached at pin 19, the TDA 16888 changes from the passive to the active state. In the passive state the IC draws a maximum current of 100 μ A while monitoring the switching thresholds and actively maintaining the driver outputs at the L-level. In the active state the chip first checks whether the intermediate circuit voltage at pin 19 lies between 20% and 120% of its nominal value (e.g. between 80V and 480V for a nominal value of 400V). If this is the case, the chip concludes that monitoring for the intermediate circuit voltage is connected (FMEA) and there is no risk to operation from an overvoltage.

If the intermediate circuit voltage is found to be satisfactory, and no excess current is detected at pin 6, then the PFC converter starts working at half the rated frequency to cut the IC current consumption. During this process the TDA 16888 is initially powered from the start-up capacitor C11A until the boost converter starts to supply it, or, should the IC switch-off threshold (11V) be reached first, it switches into the passive state and a new start-up attempt is initiated. As soon as the intermediate circuit voltage has reached 80% of its nominal value, the PWM also starts running, with both converter sections now operating at the rated frequency. A soft-start procedure is used for the PMW converter, the rise time being set using C14 at pin 13.

If the voltage at pin 13 is less than 0.4V, the chip interprets this condition as standby mode, and shuts off the PWM section. In standby mode the PFC converter again works at half the rated frequency to reduce current consumption.

While the MOSFET Q1 is switching, a modulated AC voltage appears at the secondary windings of choke L2. The voltage across the main winding of choke L2 varies during rated operation from 400V when Q1 is cut off and the AC input voltage passes through zero, to 400V when Q1 is conducting and the maximum input voltage is at its peak value. The lowest voltage across the main winding (± 200 V) arises when the input voltage is exactly half as large as the intermediate circuit voltage. This is why the standby and IC supply voltages are derived from bridge rectification of the auxiliary windings on L2, in order to use both the cut-off and conduction phase of the inductance. The voltage regulators IC5 and Q3/D11 are required because of the variation by a factor of 2 in the dc voltage obtained.

When the PFC converter is run up, the intermediate circuit voltage overshoots. Under low load it takes a considerable time to return to its nominal level, because of the slow discharge of the smoothing capacitor C3. During this period the voltage regulator would cut off the MOSFET Q1 (up to more than 100ms), which would prevent the control logic being supplied from the boost converter choke. This is why the TDA 16888 has a further control loop, using input pin 20, in addition to the two control loops for the intermediate circuit voltage and the input current. A second output path from the boost converter (D6, C4, R2) is taken via potential divider R1, R27 to detect whether Q1 is operating.

This works by the voltage at C4 being set using voltage divider R1, R27 to the nominal value of the intermediate circuit voltage, or a few percent below. The short time constant of the second output path from the boost converter ($C4 \approx 10\text{nF}$, $R2 \approx 500\text{k}\Omega$) means that any drop in the voltage at C4 is rapidly detected, and the MOSFET Q1 switched on via the PFC current regulator. If necessary this is done with such short pulses that the voltage at the main output from the boost converter does not rise, even with no load at all. The limited controllability of the boost converter during no-load conditions means that the power available at the standby output is limited. For example 5V/100mA is provided with a quite good efficiency.

Normal operation

The oscillator frequency is set by just one external resistor R24. The ramp voltages for the oscillator and the pulse width modulation (PWM) of the PFC section are generated across integrated capacitors. The duty cycle of the PFC section varies from 0 to over 90%, and for the PWM section from 0 to 50% maximum. During one switching period, the PFC MOSFET Q1 switches on first. The PWM MOSFET Q2 switches on half a period later. For greater reliability, flip-flops are used to control this timing sequence. The oscillator therefore runs at twice the rate of the external operating frequency. By integrating the capacitors, external circuitry is not required, and so the current consumption is reduced because of the smaller capacitances.

The waveform of the rectified, unsmoothed mains voltage is detected across resistors R4A, R4B, and applied to the first input of an integrated multiplier. The output voltage from the PFC voltage control amplifier is taken to the second input to the multiplier. The current at the output of the multiplier, pin 4, is a reference value having the waveform of the rectified mains voltage and an amplitude controlled by the voltage regulator. The PFC current regulator controls the rectified mains current such that the voltage drop across shunt R6 assumes exactly the same value as the voltage drop across R5 produced by the output current from the multiplier. The output current from the PFC current regulator (pin 3) sets up the duty cycle for the MOSFET Q1 by comparison with an internally generated ramp voltage.

The intermediate circuit voltage is regulated by the PFC voltage regulator (pin 17, pin 18) at a level that is greater than or equal to the peak value of the maximum input voltage ($270\text{V} \cdot \sqrt{2} = 382\text{V}$). An intermediate circuit voltage of 380V is often chosen, because one must expect a maximum voltage of this magnitude even without a PFC converter. A 450V type smoothing capacitor (C3) is used, however, to ensure that even under transient conditions, the voltage remains below the permitted capacitor voltage. In this case it is worth increasing the intermediate circuit voltage to 410V, and to design the onset threshold for overvoltage limiting to be 430V (R11, R12 to give 5.5V at pin 19). The intermediate circuit voltage still remains below 450V during transient conditions, and the benefit lies in the 40% higher hold time, which can be bridged if the mains drops out.

The PWM converter is designed to work as a single-ended forward converter. The turn-on time is determined by the oscillator, as soon as the voltage at the soft start input pin 13 and the control input pin 14 exceeds 0.4V. After the soft start phase, the voltage at control input pin 14 together with the ramp voltage at pin 15 controls the turn-off time. An improved current ramp control technique (current mode control) is used here, where the ramp voltage has an amplitude 5 times higher than those traditionally used. The current in the Q2 source path is also measured across shunt resistor R15, and detected at pin 11. At a voltage of 1V at pin 11, the integrated overcurrent comparator switches off MOSFET Q2. The signal at pin 11 is also amplified by a factor of 5 by a linear amplifier, and taken via an internal 10k resistor to pin 15. A base ramp voltage with an amplitude of 1.5V is produced across capacitor C13 connected to this pin, even when there is no transistor current (slope compensation). This voltage can rise to over 6V when the maximum current flows through Q2. This allows pulse width modulation at higher signal levels, enabling stable operation right up to no-load conditions.

The transformer Tr1 in the forward converter works at the pre-regulated intermediate circuit voltage. This means that a higher transformer ratio can be selected, reducing the current load for the MOSFET. Furthermore, a larger duty cycle can be set during normal operation because there is a smaller variation range for the input voltage. The magnetization energy can be fed back into the smoothing capacitor using a demagnetization winding and demagnetization diode D7.

In forward converters with universal input voltage range this is not possible without pre-regulation, or causes significant losses in the required demagnetization network. In our application circuit, overvoltage peaks across MOSFET Q2 and diode D7 are efficiently limited using diodes D22 and D27 and network C31, R40. On the secondary side there is one rectifying and one freewheeling diode (D8, D9; D20, D21) for each output voltage. A damping network (e.g. R41, C29; R42, C30) is connected in parallel with every diode, to attenuate commutation-induced overvoltage spikes and transients. Another RC element (R47, C34) damps the voltage decay in intermittent dc flow, to avoid irregular premagnetization of the smoothing choke. The output voltages are taken via separate windings on a common smoothing choke L3 to convert the switched voltages into a flow of current. The smoothing capacitors (e.g. C15, C28) reduce the ripple on the output voltage and serve as a storage device when the load changes rapidly. For high output currents it is advisable to divide up the smoothing capacitance with small inductances (L5, L6), to compensate for the equivalent series resistance (ESR) of the capacitors.

The output voltage with the highest stability specification is controlled directly by regulating amplifier IC2 and optocoupler IC3. The other output voltages are stabilized indirectly by the choice of winding ratio for transformer Tr1 and choke L3 according to the ratio of the output voltages. An extra comparator IC6 and optocoupler IC4 monitor the standby output voltage. When the standby switch is closed, the PWM converter is only started once the PFC converter has produced at least 90% of the nominal voltage at the standby output. Standby operation can be initiated by opening the switch. Transistor Q4 with low-pass filter at its base, prevents noise spikes and leakage currents from the optocoupler from discharging the soft-start capacitor during normal operation.

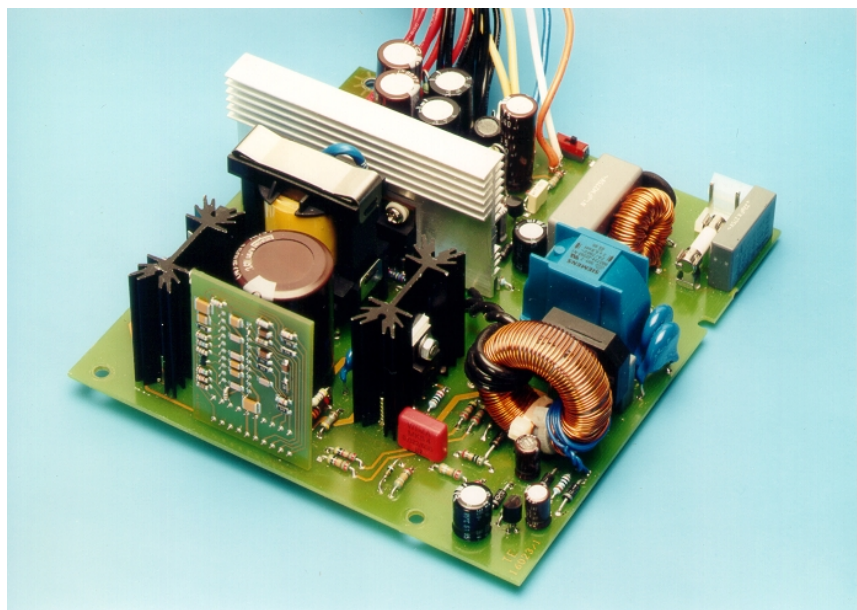
Protective features

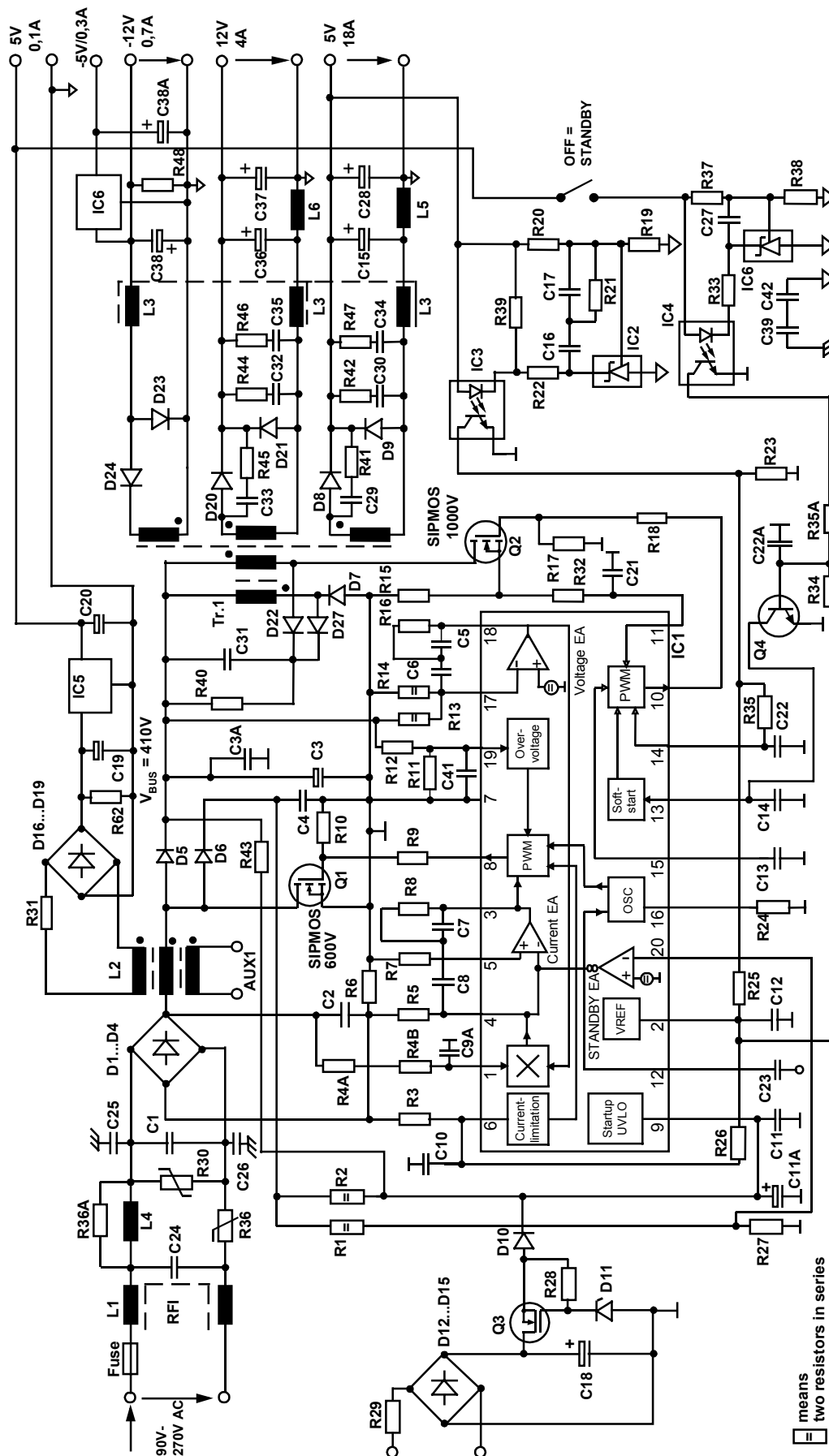
When a short circuit occurs on the output side, the primary current is limited by measuring the drop across shunt R15. In applications with several output voltages, this only works as a short-term protective measure, because the output rectifier, for example, cannot withstand the overload. Extra protection can be provided by monitoring the output voltages for a minimum value, with a delayed switch into standby mode.

To deal with overshoots in the intermediate circuit voltage, a switch-off threshold can be set as required (e.g. 5% above the nominal value) using potential divider R11, R12. If this is exceeded then the PFC converter cuts off the power to the intermediate circuit.

When transient mains surges occur which charge the smoothing capacitor C3 to 10% above the PFC switch-off threshold, the PWM MOSFET Q2 is also cut-off to protect the power supply unit. If the mains voltage rises still further, then varistor R30 can limit it. Using these protective devices, the application circuit can withstand transient mains surges of 600V and more.

Figure 1:
A 150W PC power supply design with power factor correction using TDA 16888 fits inside a typical PC power supply silver box.





Circuit Diagram of single transistor multioutput forward converter with PFC

V in	I in	P in	PF	THD	V BUS	V out1	I out1	V out2	I out2	V out3	I out3	V out4	I out4	VSby	ISby	P out	Efficiency
V AC	A rms	W	%	%	V DC	V DC	A	V DC	A	V DC	A	V DC	A	V	A	W	%
90	2,45	220,0	99,8	4,6	380,00	5,00	18,10	12,60	4,00	-12,70	0,70	-5,00	0,30	5,00	0,10	151,8	69,0
90	1,62	146,0	99,9	3,5	380,00	5,00	18,00	13,10	1,00	-13,40	0,10	-5,00	0,00	5,00	0,10	104,9	71,9
90	0,60	54,0	99,8	2,8	380,00	5,00	5,00	12,20	1,00	-12,30	0,10	-5,00	0,00	5,00	0,10	38,9	72,1
90		4,8			380,00	5,00	0,00	12,10	0,00	-11,90	0,00	-5,00	0,00	5,00	0,10	0,5	
90		2,7			380,00	0,00		0,00		0,00		0,00		5,00	0,10	0,5	
120	1,70	205,0	99,9	3,4	380,00	5,00	18,10	12,60	4,00	-12,70	0,70	-5,00	0,30	5,00	0,10	151,8	74,0
120	1,17	140,0	99,9	2,8	380,00	5,00	18,00	13,10	1,00	-13,40	0,10	-5,00	0,00	5,00	0,10	104,9	75,0
120	0,44	53,0	99,4	6,0	380,00	5,00	5,00	12,20	1,00	-12,30	0,10	-5,00	0,00	5,00	0,10	38,9	73,5
120		4,7			380,00	5,00	0,00	12,10	0,00	-11,90	0,00	-5,00	0,00	5,00	0,10	0,5	
120		2,7			380,00	0,00		0,00		0,00		0,00		5,00	0,10	0,5	
180	1,10	198,0	99,7	3,6	380,00	5,00	18,10	12,60	4,00	-12,70	0,70	-5,00	0,00	5,00	0,10	150,3	75,9
180	0,76	136,0	99,5	1,5	380,00	5,00	18,00	13,10	1,00	-13,40	0,10	-5,00	0,00	5,00	0,10	104,9	77,2
180	0,29	51,0	97,0	12,5	380,00	5,00	5,00	12,20	1,00	-12,30	0,10	-5,00	0,00	5,00	0,10	38,9	76,3
180		4,5			380,00	5,00	0,00	12,10	0,00	-11,90	0,00	-5,00	0,00	5,00	0,10	0,5	
180		2,6			380,00	0,00		0,00		0,00		0,00		5,00	0,10	0,5	
230	0,85	196,0	99,4	4,0	380,00	5,00	18,10	12,60	4,00	-12,70	0,70	-5,00	0,00	5,00	0,10	150,3	76,7
230	0,59	135,0	98,9	4,5	380,00	5,00	18,00	13,10	1,00	-13,40	0,10	-5,00	0,00	5,00	0,10	104,9	77,7
230	0,24	51,0	94,0	14,0	380,00	5,00	5,00	12,20	1,00	-12,30	0,10	-5,00	0,00	5,00	0,10	38,9	76,3
230		4,6			380,00	5,00	0,00	12,10	0,00	-11,90	0,00	-5,00	0,00	5,00	0,10	0,5	
230		2,5			380,00	0,00		0,00		0,00		0,00		5,00	0,10	0,5	
270	0,73	196,0	98,9	4,4	380,00	5,00	18,10	12,60	4,00	-12,70	0,70	-5,00	0,00	5,00	0,10	150,3	76,7
270	0,51	134,0	98,3	5,1	380,00	5,00	18,00	13,10	1,00	-13,40	0,10	-5,00	0,00	5,00	0,10	104,9	78,3
270	0,21	51,0	90,4	16,0	380,00	5,00	5,00	12,20	1,00	-12,30	0,10	-5,00	0,00	5,00	0,10	38,9	76,3
270		4,4			380,00	5,00	0,00	12,10	0,00	-11,90	0,00	-5,00	0,00	5,00	0,10	0,5	
270		2,5			380,00	0,00		0,00		0,00		0,00				0,5	

Test Results of single transistor multioutput forward converter with PFC

Bill of Materials

Component	Value	Order-Nr.	Manufacturer
IC 1 *	TDA 16888	Q67000-A9284	Infineon
IC 2	TL 431 C		TI
IC 3	CNY 17 F-3	Q62703-N50	Infineon
IC 4	CNY 17-3	Q62703-N88	Infineon
IC 5	TLE 4264 G	Q67006-A-9139	Infineon
IC 6	TL 431 C		TI
Q 1	BUZ 91 (600V/ 0,8 Ω)	Q67078-S1342-A2	Infineon
Q 2	BUZ 51 (1000V/ 4Ω)	Q67078-S1344-A2	Infineon
Q 3	BSS 129 (240V/ 20Ω, Depletion)	Q67000-S116	Infineon
Q 4 *	BC 338 (30V/ 800mA, NPN)	Q62702-C314	Infineon
D 1...D 4	GR B250 C5000/3300		
D 5	STTA506D (600V; 5A; 20ns)		ST
D 6	MUR 160 (600V; 1A; 75ns)		Motorola
D 7	BYT 11-1000 (1000V; 1A; 100ns)		ST
D 8, D 9	MBR 2535 CTL (Schottky 35V; 2x 12,5A)		Motorola
D 10	1N4148		
D 11	BZX 83 C13		
D 12...D 15	UF 4003 (100V; 1A; 50ns)		GI
D 16...D 19	UF 4003 (100V; 1A; 50ns)		GI
D 20, D 21	BYV 32-100 (100V; 2x 10A; 25ns)		Eupec, Philips
D 22	BYT 11-1000 (1000V; 1A; 100ns)		ST
D 23, D 24	MUR 120 (200V; 1A; 50ns)		Motorola
D 27	BYT 11-1000 (1000V; 1A; 100ns)		ST
L 1	2x 6,8mH/ 2A	B82724-J2202-N1	EPCOS
L 2	1mH E36/11; N27; GAP 2mm 100turns, 0,6mm Ø AUX 1: 8turns 0,33mm Ø AUX 2: 5turns 0,33mm Ø	B66389-G1000-X127	EPCOS
L 3	8µH (W3) E36/11, N27, GAP 2mm W3: 9turns 2x 2x0,9mm Ø W1: 21turns 0,7mm Ø W2: 21turns 0,3mm Ø	B66389-G1000-X127	EPCOS
L 4	500µH EF25, N27, GAP 2mm 90turns, 0,45mm Ø	B66317-G1000-X127	EPCOS
L 5	1µH 9turns 2mm Ø airchoke		
L 6	1µH 10turns 1,2mm Ø airchoke		
Fuse	2,5A MT		
Component	Value	Order-Nr.	Manufacturer
T 1	E36/11, N27, without GAP Primary: 68 turns 0,40mm Ø Demagn.: 68 turns 0,22mm Ø Sec.1: 3 turns 4x 0,8mm Ø Sec.2: 7 turns 2x 0,8mm Ø Sec.3: 7 turns 0,4mm Ø	B66389-G-X127	EPCOS

Component	Value	Order-Nr.	Manufacturer
C 1	0,33μF 275V AC, X2	B81133-D1334-M	EPCOS
C 2	not assembled		
C 3	150μF/ 450V Elko	B43501-J5157-M	EPCOS
C 3A	0,15μF/ 630V MKP	B32652-A6154-K	EPCOS
C 4	10nF/ 1000V MKP	B32652-A103-K	EPCOS
C 5 *	47nF/63V MKT	B32529-C473-K	EPCOS
C 6 *	100nF/63V MKT	B32529-C104-K	EPCOS
C 7 *	1nF/63V MKT	B32529-C102-K	EPCOS
C 8 *	10nF/63V MKT	B32529-C103-K	EPCOS
C 9 *	not assembled		
C 9A *	6,8nF/63V MKT	B32529-C682-K	EPCOS
C 10 *	10pF/100V CG	B37979-G1100-J51	EPCOS
C 11 *	0,47μF/63V MKT	B32529-C474-K	EPCOS
C 11A *	100μF/25V Elko	B41283-C5107-T90	EPCOS
C 11B *	47nF/50V X7R	B37981-F5473-K51	EPCOS
C 12 *	0,15μF/63V MKT	B32529-C154-K	EPCOS
C 13 *	100pF/50V CG	B37979-G5101-J51	EPCOS
C 14 *	100nF/63V MKT	B32529-C104-K	EPCOS
C 15	2200μF/10V Elko	B41822-A3228-M	EPCOS
C 16	68nF/63V MKT	B32529-C683-K	EPCOS
C 17	2,2nF/63V MKT	B32529-C222-K	EPCOS
C 18	100μF/63V Elko	B41822-A8107-M	EPCOS
C 19	470μF/35V Elko	B41822-A7477-M	EPCOS
C 20	100μF/25V Elko	B41822-A1107-M	EPCOS
C 21 *	220pF/50V CG	B37979-G5221-J51	EPCOS
C 22 *	4,7nF/63V MKT	B32529-C472-K	EPCOS
C 22A *	10nF MKT	B32529-C103-K	EPCOS
C 23 *	not assembled		
C 24	0,33μF 275V AC, X2	B81133-D1334-M	EPCOS
C 25, C 26	3,3nF 250V AC, Y2, lead spacing 15mm	B81121-C-B142	EPCOS
C 25, C 26	3,3nF 250V AC, Y2, lead spacing 10mm	B81122-C1332-M	EPCOS
C 27	4,7nF/63V MKT	B32529-C472-K	EPCOS
C 28	2200μF/10V Elko	B41822-A3228-M	EPCOS
C 29	1nF/63V MKT	B32529-C102-K	EPCOS
C 30	1nF/63V MKT	B32529-C102-K	EPCOS
C 31	1nF/630V Position R 40		
C 32	2,2nF/63V MKT	B32529-C222-K	EPCOS
C 33	2,2nF/63V MKT	B32529-C222-K	EPCOS
C 34	insert wire bridge		
C 35	insert wire bridge		
C 36	1000μF/16V	B41822-A4108-M	EPCOS
C 37	1000μF/16V	B41822-A4108-M	EPCOS
C 38	470μF/16V	B41822-A4477-M	EPCOS
C 39	3,3nF 250V AC, Y1	B81123-C1332-M	EPCOS
C 41 *	220pF/50V CG	B37979-G5221-J51	EPCOS
C 40	not assembled		
C 42	insert wire bridge		
C	1,5nF/630V assembled between Heatsink of Q2 and BUS Voltage		

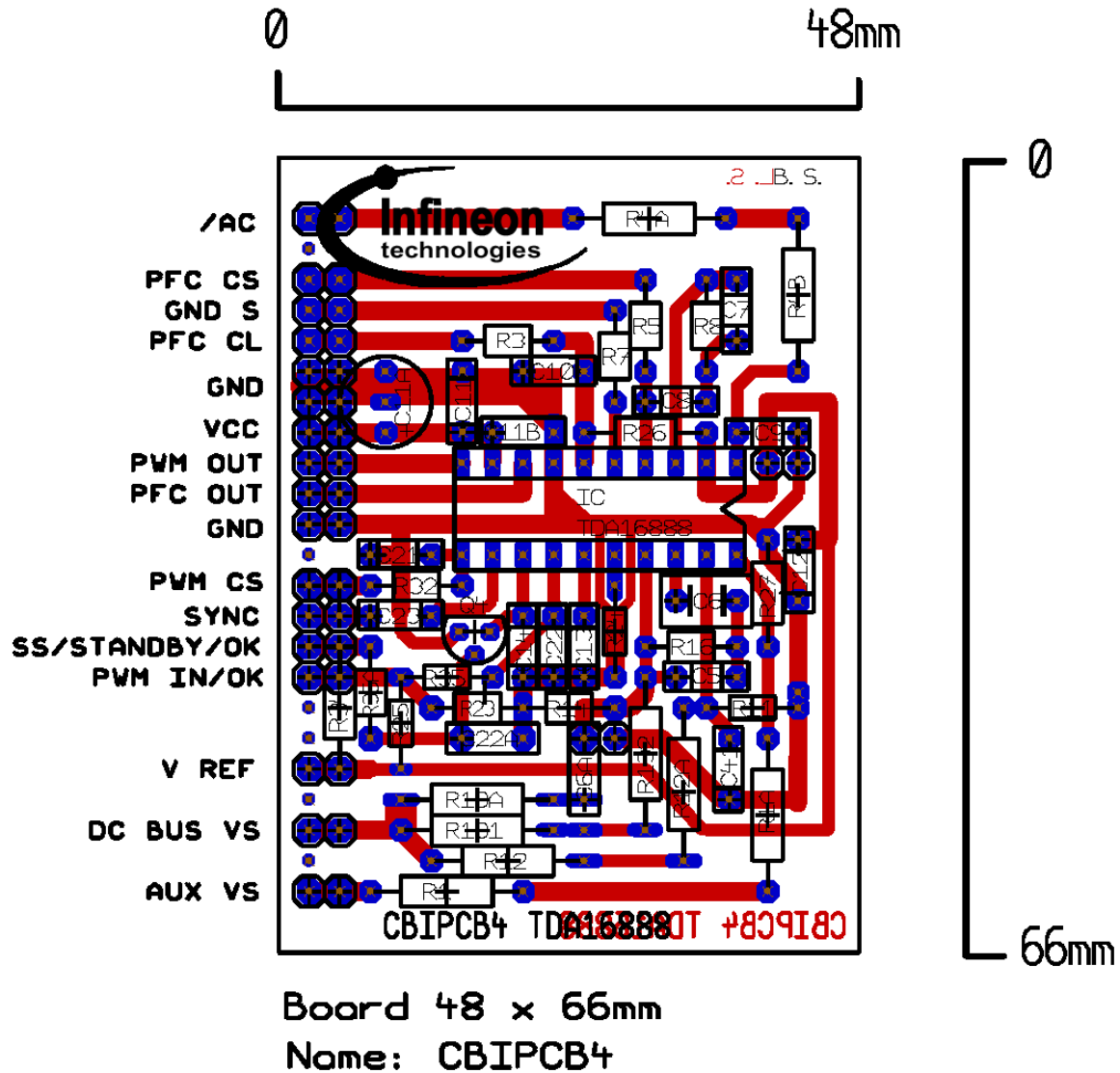
* = located on control board

Component	Value	Order-Nr.	Manufacturer
R 1	* 3825K 2x 1,91M metal		
R 2	220K		
R 2A	220K		
R 3	* 22K		
R 4A	* 390K metal		
R 4B	* 390K metal		
R 5	* 2,2K		
R 6	0,22 1 + 2x 0,56 parallel		
R 7	* 2,2K		
R 8	* 7,5K		
R 9	3,3		
R 10	18K		
R 11	* 51K metal		
R 12	* 3825K 2x 1,91M metal		
R 13	* 3825K 2x 1,91M metal		
R 14	* 51K metal		
R 15	0,50 2x 1 parallel		
R 16	* 390K		
R 17	18K		
R 18	3,3		
R 19	5,1K metal		
R 20	5,1K metal		
R 21	10K		
R 22	680		
R 23	* 33K		
R 24	* 51 K metal		
R 25	* 10K		
R 26	* 68K		
R 27	* 51K metal		
R 28	4,7K		
R 29	1		
R 30	SIOV-S14K250G5	Q69x4603	EPCOS
R 31	insert wire bridge		
R 32	* 1,1K		
R 33	470		
R 34	* 56K		
R 35	* 1,1K		
R 35A	* 680		
R 36A	56 4W		
R 37	3,9K metal		
R 38	5,1K metal		
R 39	1K1		
R 40	220K 2W		
R 41	33		
R 42	33		
R 43	not assembled		
R 43 A	330K 2W between VBUS and VCC		
R 44	56		
R 45	56		
R 46	470		
R 47	100		
R 48	470		
R 49	not assembled		

• = located on control board

Warning: Heatsink of D5 is connected to 380V BUS Voltage !

Printed Circuit Board of control circuit



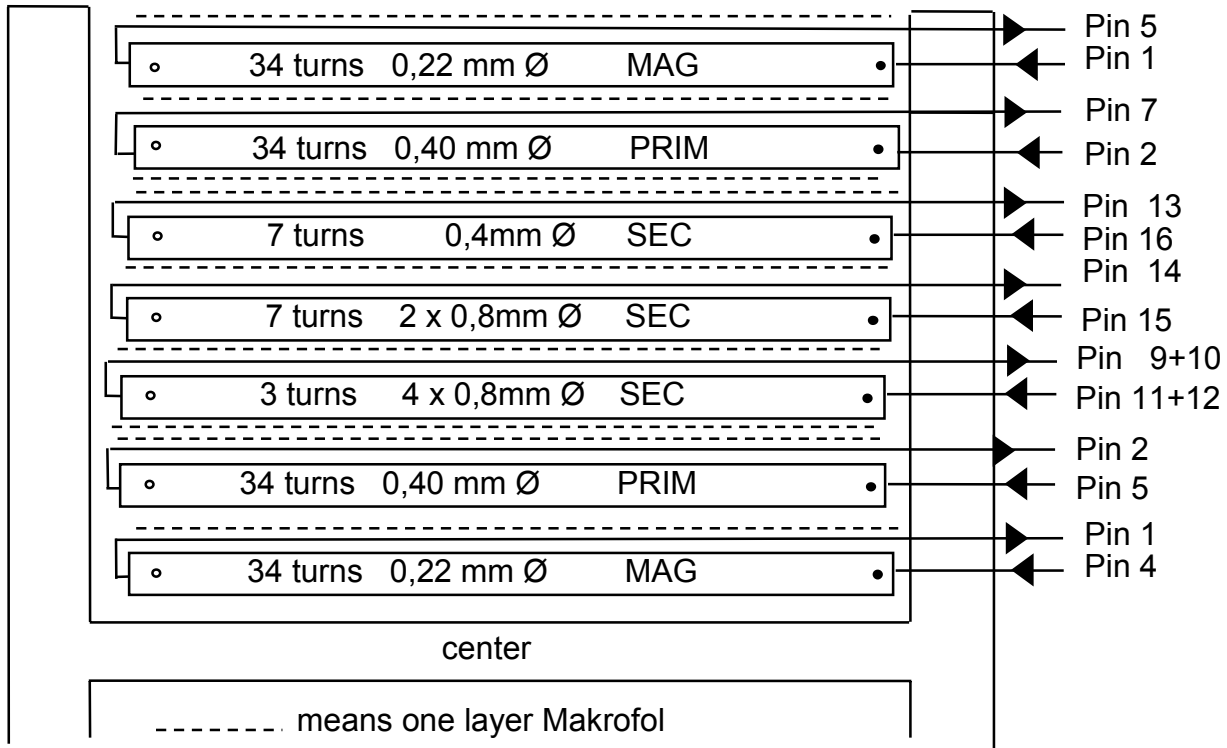


Printed Circuit Board of power circuit

Single ended feed forward Transformer

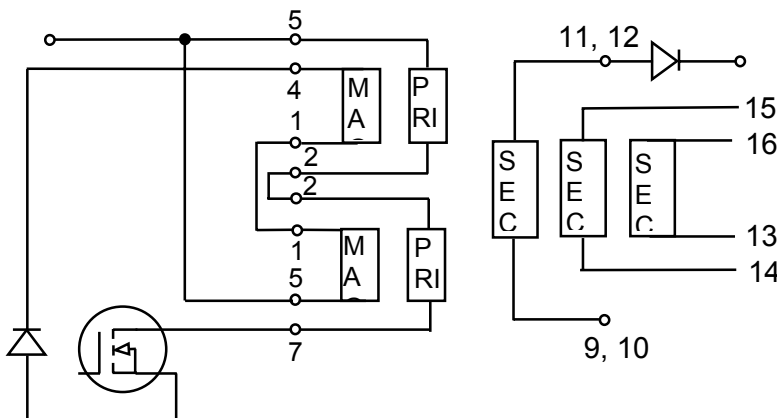
150W / 100kHz; Output voltage: 5V/18A; 12V/4A; -12V/1A

Core E36/18/11; N27; without gap; $A_{LMIN} = 2330nH$; coil former vertical



Primary winding	68 turns	0,40 mm Ø	transformer wire
Demagnetization	68 turns	0,22 mm Ø	transformer wire
Secondary winding1	3 turns	4 x 0,8 mm Ø	transformer wire
Secondary winding2	7 turns	2 x 0,8 mm Ø	transformer wire
Secondary winding3	7 turns	0,4 mm Ø	transformer wire

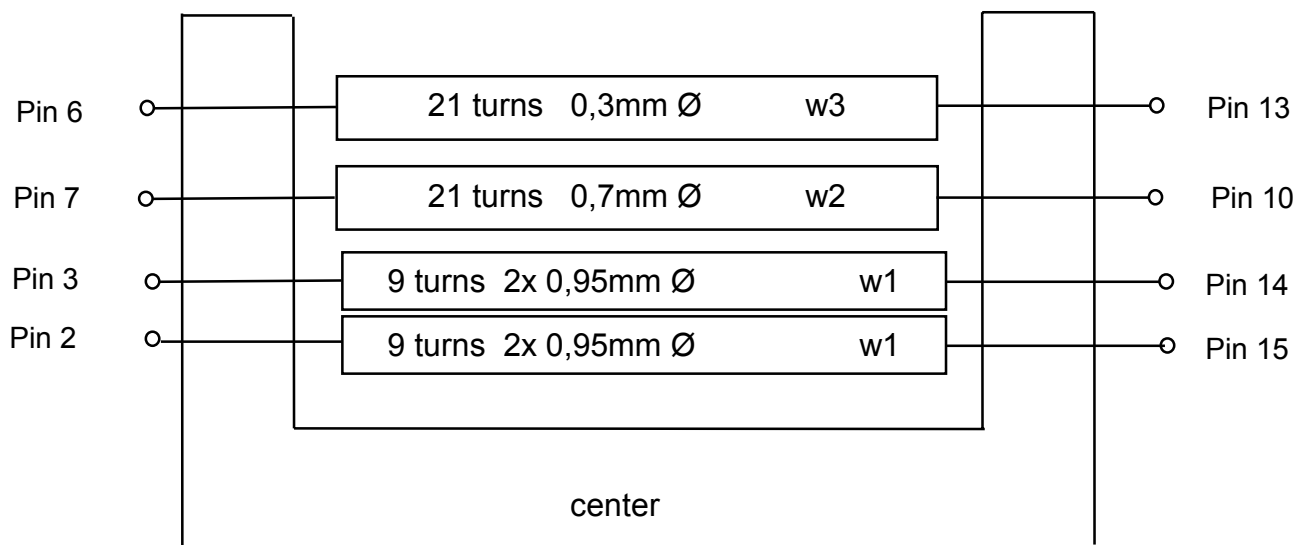
Top



Pin 1 •	• Pin 16
Pin 2 •	• Pin 15
•	• Pin 14
Pin 4 •	• Pin 13
Pin 5 •	• Pin 12
•	• Pin 11
Pin 7 •	• Pin 10
Pin 8 •	• Pin 9

Smoothing Choke of single ended forward converter

Core E36/18/11; N27; total gap = 2mm; $A_L = 100\text{nH}$; coil former horizontal;
 $L = 8\mu\text{H}$; @5V output



Winding 1: 9 turns 2 x 2 x 0,95 mm Ø transformer wire

Winding 2: 21 turns 0,7 mm Ø transformer wire

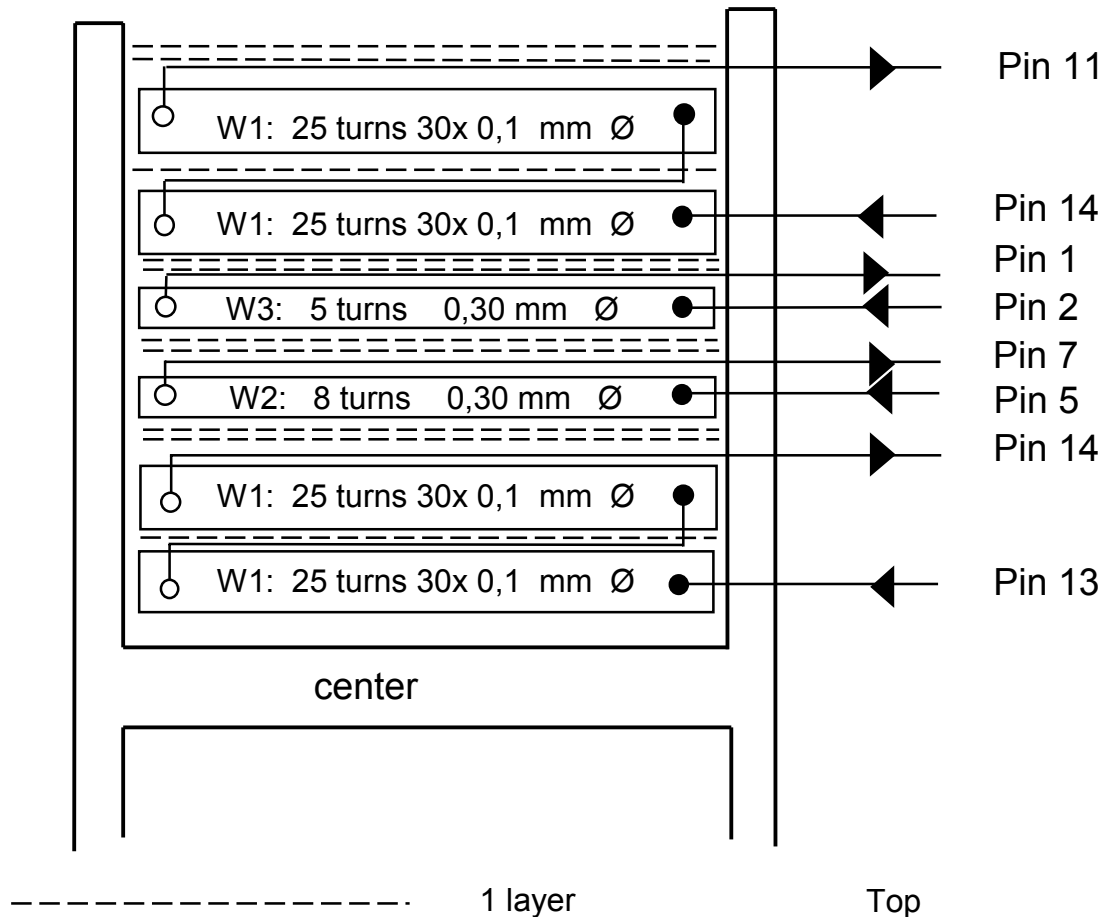
Winding 2: 21 turns 0,3 mm Ø transformer wire

Top

Pin 8 •	• Pin 9
Pin 7 •	• Pin 10
Pin 6 •	• Pin 11
Pin 5 •	• Pin 12
Pin 4 •	• Pin 13
Pin 3 •	• Pin 14
Pin 2 •	• Pin 15
Pin 1 •	• Pin 16

Boost converter choke for PFC

Core E36/18/11; N27; total gap = 2mm; $A_L = 100 \text{ nH}$;
 $L = 1 \text{ mH}$; $I_{PEAK} = 3,5 \text{ A}$; coil former vertical

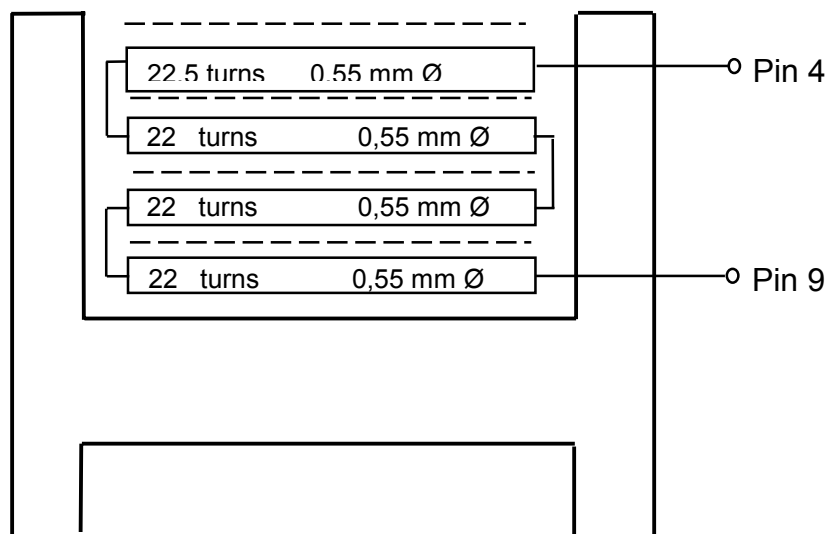


W1 : 100 turns 30 x 0,1 stranded wire w/ silk
W2 : 8 turns 0,30 transformer wire
W3 : 5 turns 0,30 transformer wire

Top	
Pin 1 •	• Pin 16
Pin 2 •	• Pin 15
•	• Pin 14
Pin 4 •	• Pin 13
Pin 5 •	• Pin 12
•	• Pin 11
Pin 7 •	• Pin 10
Pin 8 •	• Pin 9

RFI Choke $L = 470\mu\text{H}$, $I_{\text{PEAK}} = 3,5\text{A}$

Core E 25/13/7 (EF25), N27, total gap= 2mm, $A_L = 54 \text{ nH}$, coil former vertical



----- means one layer of Makrofol

88,5 turns transformer wire 0,55 mm Ø

Top

Pin 1	•	•	Pin 10
	•	•	
	•	•	
	•	•	
Pin 5	•	•	Pin 6



References:

[1] nnn

Revision History		
Application Note AN-TDA16888-0-010323		
Actual Release: V1.1 Date:2001-03-23		Previous Release: V0.1
Page of actual Release	Page of prev. Release	Subjects changed since last release

For questions on technology, delivery and prices please contact the Infineon Technologies Offices in Germany or the Infineon Technologies Companies and Representatives worldwide: see the address list on the last page or our webpage at

<http://www.infineon.com>

CoolMOS™ and CoolSET™ are trademarks of Infineon Technologies AG.

Edition 2000-03--03

**Published by Infineon Technologies AG,
St.-Martin-Strasse 53,
D-81541 München**

**© Infineon Technologies AG 2000.
All Rights Reserved.**

Attention please!

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives worldwide (see address list).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Infineon Technologies AG sales offices worldwide – partly represented by Siemens AG

A Siemens AG Österreich Erdberger Lande 26 A-1031 Wien T (+43)1-17 07-3 56 11 Fax (+43)1-17 07-5 59 73 AUS Siemens Ltd. 885 Mountain Highway Bayswater, Victoria 3153 T (+61)3-97 21 21 11 Fax (+61)3-97 21 72 75 B Siemens Electronic Components Benelux Charleroisesteeweg 116/ Chaussée de Charleroi 116 B-1060 Brussel/Bruxelles T (+32)2-5 36 69 05 Fax (+32)2-5 36 28 57 Email: components@siemens.nl BR Siemens Ltda. Semicondutores Avenida Mutinga, 3800-Pirituba 05110-901 São Paulo-SP T (+55)11-39 08 25 64 Fax (+55)11-39 08 27 28 CDN Infineon Technologies Corporation 320 March Road, Suite 604 Canada, Ontario K2K 2E2 T (+1)6 13-5 91 63 86 Fax (+1)6 13-5 91 63 89 CH Siemens Schweiz AG Bauelemente Freilagerstrasse 40 CH-8047 Zürich T (+41)1-4 953065 Fax (+41)1-4 955050 D Infineon Technologies AG Völklinger Str. 2 D-40219 Düsseldorf T (+49)2 11-3 99 29 30 Fax (+49)2 11-3 99 14 81 Infineon Technologies AG Werner-von-Siemens-Platz 1 D-30880 Laatzen (Hannover) T (+49)5 11-8 77 22 22 Fax (+49)5 11-8 77 15 20 Infineon Technologies AG Von-der-Tann-Straße 30 D-90439 Nürnberg T (+49)9 11-6 54 76 99 Fax (+49)9 11-6 54 76 24 Infineon Technologies AG Weissacher Straße 11 D-70499 Stuttgart T (+49)7 11-1 37 33 14 Fax (+49)7 11-1 37 24 48 D Infineon Technologies AG Halbleiter Distribution Richard-Strauss-Straße 76 D-81679 München T (+49)89-92 21 40 86 Fax (+49)89-92 21 20 71 DK Siemens A/S Borupvang 3 DK-2750 Ballerup T (+45)44 77-44 77 Fax (+45)44 77-40 17 E Siemens S.A. Dpto. Componentes Ronda de Europa, 5 E-28760 Tres Cantos-Madrid T (+34)91-5 14 71 51 Fax (+34)91-5 14 70 13	F Infineon Technologies France, 39/47, Bd. Ornano F-93527 Saint-Denis CEDEX2 T (+33)1-49 22 31 00 Fax (+33)1-49 22 28 01 FIN Siemens Components Scandinavia P.O. Box 60 FIN-02601 Espoo (Helsinki) T (+358)10-5 11 51 51 Fax (+358)10-5 11 24 95 Email: scs@components.siemens.se GB Infineon Technologies Siemens House Oldbury GB-Bracknell, Berkshire RG12 8FZ T (+44)13 44-39 66 18 Fax (+44)13 44-39 66 32 H Simacomp Kft. Lajos u. 103 H-1036 Budapest T (+36)1-4 57 16 90 Fax (+36)1-4 57 16 92 HK Infineon Technologies Hong Kong Ltd. Suite 302, Level 3, Festival Walk, 80 Tat Chee Avenue, Yam Yat Tsuen, Kowloon Tong Hong Kong T (+8 52)28 32 05 00 Fax (+8 52)28 27 97 62 I Siemens S.A. Semiconductor Sales Via Piero e Alberto Pirelli, 10 I-20126 Milano T (+39)02-66 76 -1 Fax (+39)02-66 76 43 95 IND Siemens Ltd. Components Division No. 84 Keonics Electronic City Hosur Road Bangalore 561 229 T (+91)80-8 52 11 22 Fax (+91)80-8 52 11 80 Siemens Ltd. CMP Div, 5th Floor 4A Ring Road, IP Estate New Delhi 110 002 T (+91)11-3 31 99 12 Fax (+91)11-3 31 96 04 Siemens Ltd. CMP Div, 4th Floor 130, Pandurang Budhkar Marg, Worli Mumbai 400 018 T (+91)22-4 96 21 99 Fax (+91)22-4 96 22 01 IRL Siemens Ltd. Electronic Components Division 8, Raglan Road IRL-Dublin 4 T (+353)1-2 16 23 42 Fax (+353)1-2 16 23 49 IL Nisko Ltd. 2A, Habarzel St. P.O. Box 58151 61580 Tel Aviv -Israel T (+9 72)3 -7 65 73 00 Fax (+9 72)3 -7 65 73 33	J Siemens Components K.K. Talanawa Park Tower 12F & 17F 3-20-14, Higashi-Gotanda, Shinagawa-ku Tokyo T (+81)3-54 49 64 11 Fax (+81)3 -54 49 64 01 ML Infineon Technologies AG Sdn Bhd Bayan Lepas Free Industrial Zone1 11900 Penang T (+60)4 -6 44 99 75 Fax (+60)4 -6 41 48 72 N Siemens Components Scandinavia Østre Aker vei 24 Postboks 10, Veitvet N-0518 Oslo T (+47)22-63 30 00 Fax (+47)22-68 49 13 Email: scs@components.siemens.se NL Siemens Electronic Components Benelux Postbus 16068 NL-2500 BB Den Haag T (+31)70-3 33 20 65 Fax (+31)70-3 33 28 15 Email: components@siemens.nl NZ Siemens Auckland 300 Great South Road Greenland Auckland T (+64)9-5 20 30 33 Fax (+64)9-5 20 15 56 P Siemens S.A. an Componentes Electronicos R. Irmaos Siemens, 1 Alfragide P-2720-093 Amadora T (+351)1-4 17 85 90 Fax (+351)1-4 17 80 83 PK Siemens Pakistan Engineering Co. Ltd. PO Box 1129, Islamabad 44000 23 West Jinnah Ave Islamabad T (+92)51-21 22 00 Fax (+92)51-21 16 10 PL Siemens SP. z o.o. ul. Zupnicza 11 PL-03-821 Warszawa T (+48)22-8 70 91 50 Fax (+48)22-8 70 91 59 ROK Siemens Ltd. Asia Tower, 10th Floor 726 Yeoksam-dong, Kang-nam Ku CPO Box 3001 Seoul 135-080 T (+82)2-5 27 77 00 Fax (+82)2-5 27 77 79 RUS INTECH electronics ul. Smolnaya, 24/1203 RUS-125 445 Moskva T (+7)0 95 -4 51 97 37 Fax (+7)0 95 -4 51 86 08 S Siemens Components Scandinavia Österögatan 1, Box 46 S-164 93 Kista T (+46)8-7 03 35 00 Fax (+46)8-7 03 35 01 Email: scs@components.siemens.se	RC Infineon Technologies Asia Pacific Pte. Ltd. Taiwan Branch 10F, No. 136 Nan King East Road Section 23, Taipei T (+8 86)2-27 73 66 06 Fax (+8 86)2-27 71 20 76 SGP Infineon Technologies Asia Pacific, Pte. Ltd. 168 Kallang Way Singapore 349 253 T (+65)8 40 06 10 Fax (+65)7 42 62 39 USA Infineon Technologies Corporation 1730 North First Street San Jose, CA 95112 T (+1)4 08-5 01 60 00 Fax (+1)4 08-5 01 24 24 Siemens Components, Inc. Optoelectronics Division 19000 Homestead Road Cupertino, CA 95014 T (+1)4 08-2 57 79 10 Fax (+1)4 08-7 25 34 39 Siemens Components, Inc. Special Products Division 186 Wood Avenue South Iselin, NJ 08830-2770 T (+1)7 32-9 06 43 00 Fax (+1)7 32-6 32 28 30 VRC Infineon Technologies Hong Kong Ltd. Beijing Office Room 2106, Building A Vantone New World Plaza No. 2 Fu Cheng Men Wai Da Jie Jie 100037 Beijing T (+86)10 -68 57 90 -06,-07 Fax (+86)10 -68 57 90 08 Infineon Technologies Hong Kong Ltd. Chengdu Office Room 14J1, Jinyang Mansion 58 Tudu Street Chengdu, Sichuan Province 610 016 T (+86)28-6 61 54 46 /79 51 Fax (+86)28 -6 61 01 59 Infineon Technologies Hong Kong Ltd. Shanghai Office Room 1101, Lucky Target Square No. 500 Chengdu Road North Shanghai 200003 T (+86)21-63 6126 18 /19 Fax (+86)21-63 61 11 67 Infineon Technologies Hong Kong Ltd. Shenzhen Office Room 1502, Block A Tian An International Building Renim South Road Shenzhen 518 005 T (+86)7 55-2 28 91 04 Fax (+86)7 55-2 28 02 17 ZA Siemens Ltd. Components Division P.O.B. 3438 Halfway House 1685 T (+27)11-6 52 -27 02 Fax (+27)11-6 52 20 42
--	---	---	---